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## P.E.S. College of Engineering, Mandya - 571 401

(An Autonomous Institution affiliated to VTU, Belgaum)

**First Semester, M. Tech - Electronics and Communication Engineering**

**(VLSI Design and Embedded Systems)**

**Semester End Examination; Jan/Feb. - 2016**

**CMOS VLSI Design**

*Time: 3 hrs*

*Max. Marks: 100*

*Note: Answer FIVE full questions, selecting ONE full question from each unit.*

### UNIT - I

- |   |    |  |   |
|---|----|--|---|
| 1 | a. | Derive an expression for threshold voltage in terms of built in potential and work function.             | 8 |
|   | b. | Analyze the impact of variation in $\beta$ on the transfer characteristics of CMOS inverter.             | 6 |
|   | c. | With the output characteristic and equivalent circuit. Briefly explain the working of transmission gate. | 6 |
| 2 | a. | Obtain the equivalent circuit of CMOS inverter in all five regions of operations.                        | 6 |
|   | b. | With the schematic and transfer characteristics. Explain the working of differential inverter.           | 8 |
|   | c. | Explain the different approaches in realizing BiCMOS inverter.   | 6 |

### UNIT - II

- |   |    |   |   |
|---|----|---|---|
| 3 | a. | What is the need of design rules of fabrication technology? Mention the two types of design rule. | 6 |
|   | b. | Explain 2 phases of diffusion procession in fabrication of VLSI circuits.                         | 8 |
|   | c. | Justify "The delay time and transit time are interchangeable".                                    | 6 |
| 4 | a. | Determine the scaling factor for the following design parameters :                                |   |
|   |    | (i) Gate delay  | 6 |
|   |    | (ii) Saturation Current   |   |
|   |    | (iii) Switching energy per gate   |   |
|   | b. | Discuss the alternate ways of realizing gate.   | 6 |
|   | c. | Derive an expression for total delay in a cascaded pass transistors (Connected in series).        | 8 |

### UNIT - III

- |   |    |  |   |
|---|----|--|---|
| 5 | a. | Draw the schematic of CMOS NOR2 gate with associated parasitic capacitances. What will be the value of $V_{th}$ in terms of $V_{DD}$ ? | 6 |
|   | b. | Explain the working of AOI based implementation of the closed NOR based SR latch.  | 8 |
|   | c. | Justify "Dynamic CMOS logic gates driven by same signal cannot be cascaded directly".  | 6 |
| 6 | a. | Obtain the CMOS schematic and its corresponding Euler path for the function  |   |
|   |    | $Y = \overline{BC + A(D + E)}.$  | 4 |

- b. Discuss the timing limitations of NOR based clocked JK latch circuit along with timing diagram. 8
- c. Analyze the pipelined architecture of NORA CMOS logic (NP-DOMINO logic). 8

**UNIT - IV**

- 7 a. Explain the working of common source amplifier using MOSFET and derive an expression for gain. 10
- b. Derive an expression for trans conductance in CMOS differential amplifier with relevant diagrams and waveform. 10
- 8 a. Current mirrors are used in the design of CMOS circuits. Why? Explain with necessary schematic. 10
- b. Starting from fundamentals derive an expression for  $V_{REF}$  in terms of  $V_{GO}$  and  $V_{to}$  with respect to Band gap reference. 10

**UNIT - V**

- 9 a. With cross sectional view, explain latch up in n-well CMOS inverter. Mention the causes for latch up. 12
- b. Discuss the two important schemes adopted for clock distribution. 8
- 10 a. Analyze the charge sharing in CMOS circuit design. 8
- b. Discuss the different types of clock generation. 12

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